

Phase Characteristics of I-Band Pulsed Gate GaAs FET Power Amplifiers

R.L. Camisa, R.L. Ernst, J. Goel and H.J. Wolkstein. "Phase Characteristics of I-Band Pulsed Gate GaAs FET Power Amplifiers." 1978 MTT-S International Microwave Symposium Digest 78.1 (1978 [MWSYM]): 147-149.

The measured phase sensitivities and transients of FET power amplifiers having pulsed gate voltages are very low and are suitable for phased array applications. Gate pulsing requires that the FETs have good rf performance and a drain-to-gate breakdown voltage large enough to support the sum of the gate voltage, drain voltage, and maximum rf voltage swing.

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